

IN THE TITLE:

Pursuant to 37 C.F.R. §§ 1.121 and 1.125 (as amended to date), please amend the title of the above-referenced application as follows:

~~METHOD OF DECONTAMINATING PROCESS CHAMBERS, METHODS OF REDUCING~~
~~DEFECTS IN~~SEMICONDUCTOR DEVICES AND STRUCTURES INCLUDING
SUBSTANTIALLY DEFECT-FREE AND CONTAMINANT-FREE ANTI-REFLECTIVE
~~COATINGS, AND RESULTING SEMICONDUCTOR STRUCTURES~~

IN THE SPECIFICATION:

Please amend paragraph [0040] as follows:

[0040] Referring now to FIG. 7, as is known in the art, as regions 38 are exposed to electromagnetic radiation 36, various features 29 of mask 28, such as walls that define apertures of mask 28, are defined. Due to the substantial reduction in the number or size of particles and surface roughness features in silicon nitride layer 26, the silicon nitride layer has a substantially smooth surface, and any electromagnetic radiation 36 that is reflected by silicon nitride layer 26 or DARC film 24 passes back into photoresist material 30 in a direction substantially perpendicular to the surface of silicon nitride layer 26. Accordingly, features 29 of mask 28 have substantially the desired dimensions and resolution. Moreover, the thickness of mask 28 is substantially uniform.